### **Features**

- Supply Voltage 5V
- Very Low Power Consumption 125 mW
- Very Good Image Rejection By Means of Phase Control Loop for Precise 90° Phase Shifting
- Duty-cycle Regeneration for Single-ended LO Input Signal
- Low LO Input Level -10 dBm
- LO Frequency from 70 MHz to 1 GHz
- Power-down Mode
- 25 dB Gain Control
- Very Low I/Q Output DC Offset Voltage Typically < 5 mV

### **Benefits**

- Low Current Consumption
- Easy to Implement
- Perfect Performance for Large Variety of Wireless Applications

Electrostatic sensitive device.

Observe precautions for handling.



# 1. Description

The silicon monolithic integrated circuit U2794B is a quadrature demodulator manufactured using Atmel's advanced UHF technology. This demodulator features a frequency range from 70 MHz to 1000 MHz, low current consumption, selectable gain, power-down mode and adjustment-free handling. The IC is suitable for direct conversion and image rejection applications in digital radio systems up to 1 GHz such as cellular radios, cordless telephones, cable TV and satellite TV systems.



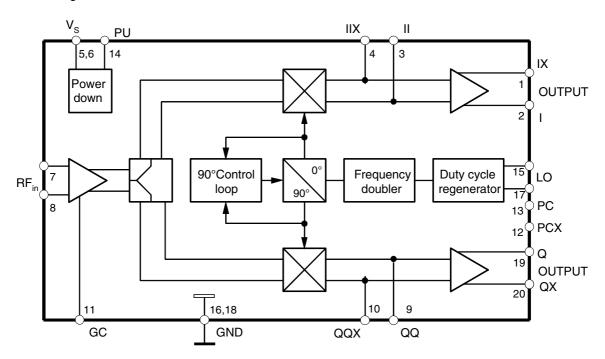
# 1000-MHz Quadrature Demodulator

U2794B





Figure 1-1. Block Diagram



# 2. Pin Configuration

Figure 2-1. Pinning SSO20

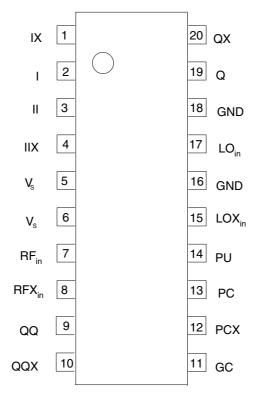


Table 2-1.Pin Description

	1 111 200011	
Pin	Symbol	Function
1	IX	IX output
2	I	I output
3	II	II lowpass filter I
4	IIX	IIX lowpass filter I
5	V <sub>S</sub>	Supply voltage
6	V <sub>S</sub>	Supply voltage
7	RF <sub>in</sub>	RF input
8	RFX <sub>in</sub>	RFX input
9	QQ	QQ lowpass filter Q
10	QQX	QQX lowpass filter Q
11	GC	GC gain control
12	PCX	PCX phase control
13	PC	PC phase control
14	PU	PU power up
15	LOX <sub>in</sub>	LOX input
16	GND	Ground
17	LO <sub>in</sub>	LO input
18	GND	Ground
19	Q	Q output
20	QX	QX output





# 3. Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Parameters	Symbol	Value	Unit	
Supply voltage	V <sub>S</sub>	6	V	
Input voltage	V <sub>i</sub>	0 to V <sub>S</sub>	V	
Junction temperature	T <sub>j</sub>	+125	°C	
Storage-temperature range	T <sub>stg</sub>	-40 to +125	°C	

## 4. Thermal Resistance

Parameters	Symbol	Value	Unit
Junction ambient SSO20	$R_{thJA}$	140	K/W

# 5. Operating Range

Parameters	Symbol	Value	Unit
Supply-voltage range	$V_S$	4.75 to 5.25	V
Ambient-temperature range	T <sub>amb</sub>	-40 to +85	°C

## 6. Electrical Characteristics

Test conditions (unless otherwise specified);  $V_S = 5V$ ,  $T_{amb} = 25$ °C, referred to test circuit System impedance  $Z_O = 50\Omega$ ,  $f_{iLO} = 950$  MHz,  $P_{iLO} = -10$  dBm

No.	Parameters	Test Conditions	Pin	Symbol	Min.	Тур.	Max.	Unit	Type*
1.1	Supply-voltage range		5, 6	V <sub>S</sub>	4.75		5.25	V	Α
1.2	Supply current		5, 6	I <sub>S</sub>	22	30	35	mA	Α
2	Power-down Mode								
2.1	"OFF" mode supply current	$V_{PU} \le 0.5V$ $V_{PU} = 1.0 V^{(1)}$	14, 5 6	I <sub>SPU</sub>		≤ 1 20		μ <b>Α</b> μ <b>Α</b>	B D
3	Switch Voltage								
3.1	"Power ON"		14	V <sub>PON</sub>	4			V	D
3.2	"Power DOWN"		14	$V_{POFF}$			1	V	D
4	LO Input, LO <sub>in</sub>								
4.1	Frequency range		17	f <sub>iLO</sub>	70		1000	MHz	D
4.2	Input level	(2)	17	$P_{iLO}$	-12	-10	<b>-</b> 5	dBm	D
4.3	Input impedance	See Figure 6-10	17	Z <sub>iLO</sub>		50		Ω	D
4.4	Voltage standing wave ratio	See Figure 6-3	17	VSWR <sub>LO</sub>		1.2	2		D
4.5	Duty-cycle range		17	DCR <sub>LO</sub>	0.4		0.6		D
5	RF Input, RF <sub>in</sub>		•	•		•	•	•	11
5.1	Noise figure (DSB) symmetrical output	at 950 MHz <sup>(3)</sup> at 100 MHz	7, 8	NF		12 10		dB	D
5.2	Frequency range	$f_{iRF} = f_{iLO} \pm BW_{YQ}$	7, 8	f <sub>iRF</sub>	40		1030	MHz	D
5.3	-1 dB input compression point	High gain Low gain	7, 8	P <sub>1dBHG</sub> P <sub>1dBLG</sub>		-8 +3.5		dBm	D
5.4	Second order IIP	(4)	7, 8	IIP <sub>2HG</sub>		35		dBm	D
5.5	Third order IIP	High gain Low gain	7, 8	IIP <sub>3HG</sub> IIP <sub>3LG</sub>		+3 +13		dBm	D
5.6	LO leakage	Symmetric input Asymmetric input	7, 8	L <sub>OL</sub>		≤ -60 ≤ -55		dBm	D
5.7	Input impedance	see Figure 6-10	7, 8	Z <sub>iRF</sub>		500110.8		ΩlpF	D

<sup>\*)</sup> Type means: A = 100% tested, B = 100% correlation tested, C = Characterized on samples, D = Design parameter

Notes: 1. During power-down status a load circuitry with DC-isolation to GND is assumed, otherwise a current of I  $\approx$  (VS -0.8V)/RI has to be added to the above power-down current for each output I, IX, Q, QX.

- 2. The required LO-Level is a function of the LO frequency (see Figure 6-6).
- 3. Measured with input matching. For 950 MHz, the optional transmission line T3 at the RF input may be used for this purpose. Noise figure measurements without using the differential output signal result in a worse noise figure.
- 4. Using pins 7 and 8 as a symmetric RF input, the second-order IIP can be improved.
- 5. Due to test board parasitics, this bandwidth may be reduced and not be equal for I, IX, Q, QX. If symmetry and full bandwidth is required, the lowpass pins 3, 4 and 9, 10 should be isolated from the board. the bandwidth of the I/Q outputs can be increased further by using a resistor between pins 3, 4, 9 and 10. These resistors shunt the internal loads of RI  $\sim$  5.4 k $\Omega$  The decrease in gain here has to be considered.
- 6. The internal current of the output emitter followers is 0.6 mA. This reduces the undistorted output voltage swing at a  $50\Omega$  load to approximately 30 mV. For low signal distortion the load impedance should be RI  $\geq 5 \text{ k}\Omega$
- 7. Referred to the level of the output vector  $\sqrt{I^2 + Q^2}$
- 8. The low-gain status is achieved with an open or high-ohmic pin 11. A recommended application circuit for switching between high and low gain status is shown in Figure 6-1.





## 6. Electrical Characteristics (Continued)

Test conditions (unless otherwise specified);  $V_S = 5V$ ,  $T_{amb} = 25^{\circ}C$ , referred to test circuit System impedance  $Z_O = 50\Omega$ ,  $f_{iLO} = 950$  MHz,  $P_{iLO} = -10$  dBm

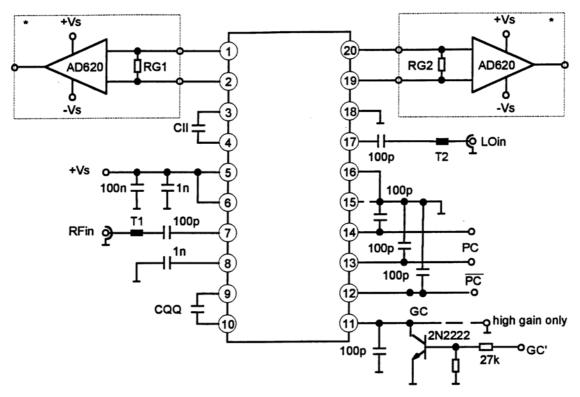
No.	Parameters	Test Conditions	Pin	Symbol	Min.	Тур.	Max.	Unit	Type*
6	I/Q Outputs (I, IX, Q,	QX) Emitter Follower I	= 0.6 mA						
6.1	3-dB bandwidth w/o external C		1, 2, 19, 20	BWI/Q	≥ 30			MHz	D
6.2	I/Q amplitude error		1, 2, 19, 20	Ae	-0.5	≤±0.2	+0.5	dB	В
6.3	I/Q phase error		1, 2, 19, 20	Pe	-3	≤ ±1.5	+3	Deg	В
6.4	I/Q maximum output swing	Symm. output $R_L > 5 \text{ k}\Omega$	1, 2, 19, 20	V <sub>PP</sub>			2		D
6.5	DC output voltage		1, 2, 19, 20	V <sub>OUT</sub>	2.5	2.8	3.1	V	А
6.6	DC output offset voltage	(6)	1, 2, 19, 20	V <sub>offset</sub>		< 5		mV	Test spec.
6.7	Output impedance	see Figure 6-10	1, 2, 19, 20	Z <sub>out</sub>		50		Ω	D
7	Gain Control, GC	•							
7.1	Control range power Gain high Gain low	(7)	11	GCR G <sub>H</sub> G <sub>L</sub>		25 23 –2		dB dBm dBm	D B D
7.2	Switch Voltage								
7.3	"Gain high"		11				1	V	
7.4	"Gain low"	(8)	11 < open						
7.5	Settling Time, ST								
7.6	Power "OFF" - "ON"			T <sub>SON</sub>		< 4		μs	D
7.7	Power "ON" - "OFF"			T <sub>SOFF</sub>		< 4		μs	D

<sup>\*)</sup> Type means: A = 100% tested, B = 100% correlation tested, C = Characterized on samples, D = Design parameter

Notes: 1. During power-down status a load circuitry with DC-isolation to GND is assumed, otherwise a current of I  $\approx$  (VS -0.8V)/RI has to be added to the above power-down current for each output I, IX, Q, QX.

- 2. The required LO-Level is a function of the LO frequency (see Figure 6-6).
- 3. Measured with input matching. For 950 MHz, the optional transmission line T3 at the RF input may be used for this purpose. Noise figure measurements without using the differential output signal result in a worse noise figure.
- 4. Using pins 7 and 8 as a symmetric RF input, the second-order IIP can be improved.
- 5. Due to test board parasitics, this bandwidth may be reduced and not be equal for I, IX, Q, QX. If symmetry and full bandwidth is required, the lowpass pins 3, 4 and 9, 10 should be isolated from the board. the bandwidth of the I/Q outputs can be increased further by using a resistor between pins 3, 4, 9 and 10. These resistors shunt the internal loads of RI  $\sim$  5.4 k $\Omega$  The decrease in gain here has to be considered.
- 6. The internal current of the output emitter followers is 0.6 mA. This reduces the undistorted output voltage swing at a  $50\Omega$  load to approximately 30 mV. For low signal distortion the load impedance should be RI  $\geq$  5 k $\Omega$
- 7. Referred to the level of the output vector  $\sqrt{l^2 + Q^2}$
- 8. The low-gain status is achieved with an open or high-ohmic pin 11. A recommended application circuit for switching between high and low gain status is shown in Figure 6-1.

Figure 6-1. Test Circuit



<sup>\*</sup> optional for single-ended tests (notice 3 dB bandwidth of AD620)

T1, T2 = transmission line  $Z_O = 50\Omega$ 

If no GC function is required, connect Pin 11 to GND.

For high and low gain status GC  $\acute{}$  is to be switched to GND respectively to  $V_S$ .

Figure 6-2. I and Q phase for  $f_{RF} > f_{LO}$ . For  $f_{RF} < f_{LO}$  the phase is inverted.

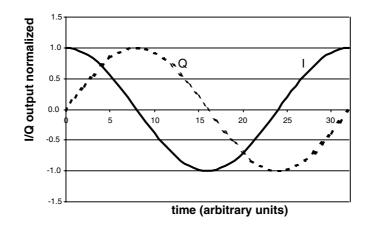
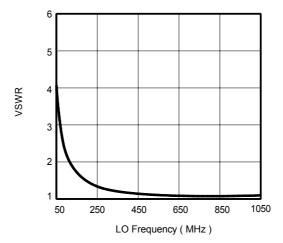






Figure 6-3. Typical VSWR Frequency Response of the LO Input



**Figure 6-4.** Noise Figure versus LO Frequency; o: Value at 950 MHz with RF Input Matching with T3

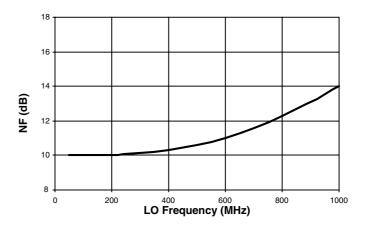


Figure 6-5. Typical Suitable LO Power Range versus Frequency

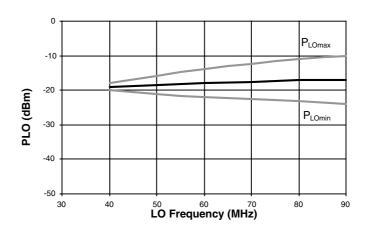
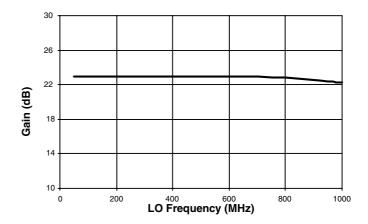


Figure 6-6. Gain versus LO Frequency; x: Value at 950 MHz with RF Input Matching with T3



**Figure 6-7.** Typical Output Signal versus LO Frequency for  $P_{RF} = -15$  dBm and PLO = -15 dBm

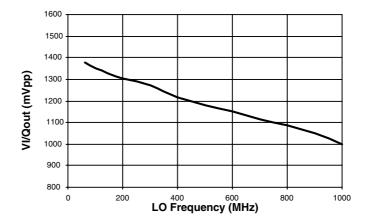
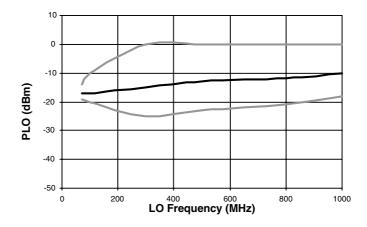


Figure 6-8. Typical Suitable LO Power Range versus Frequency







**Figure 6-9.** Typical Output Voltage (single ended) versus  $P_{RF}$  at  $T_{amb} = 25^{\circ}C$  and PLO = -15 dBm

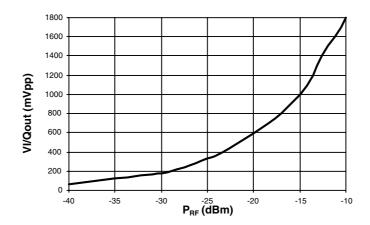
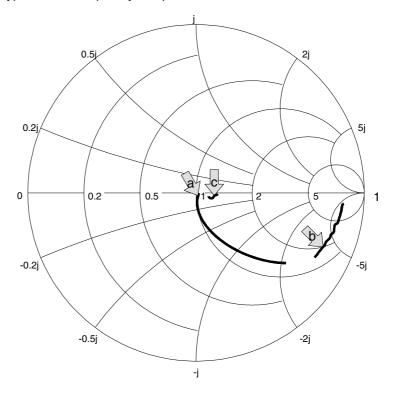


Figure 6-10. Typical S11 Frequency Response



a: LO input, LO frequency from 100 MHz to 1100 MHz, marker: 950 MHz b: RF input, RF frequency from 100 MHz to 1100 MHz, marker: 950 MHz c: I/Q Outputs, Baseband Frequency from 5 MHz to 55 MHz, marker: 25 MHz

Figure 6-11. Evaluation Board Layout

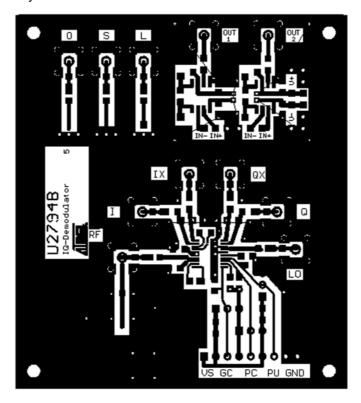
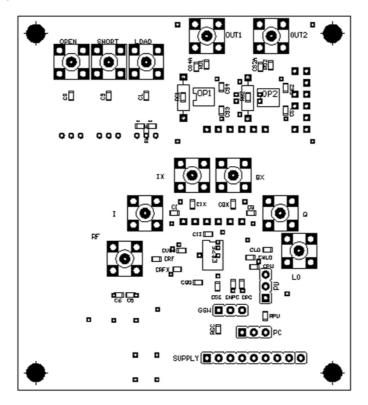


Figure 6-12. Evaluation Board





## 6.1 External Components

CUCC 100 nF
CRFX 1 nF
CLO 100 pF
CNLO 1 nF
CRF 100 pF
CII, CQQ optional external lowpass filters
T3 transmission line for RF-input m

T3 transmission line for RF-input matching, to connect optionally CI, CIX optional for AC-coupling at

CQ, CQX baseband outputs

CPDN 100 pF not connected CGC 100 pF

CPC 100 pF not connected CNPC 100 pF not connected gain switch

### 6.2 Calibration Part

CO, CS, CL 100 pF RL  $50\Omega$ 

## 6.3 Conversion to Single Ended Output

(see datasheet of AD620)

OP1, OP2 AD620 RG1, RG2 prog. gain, see datasheet, for 5.6 k $\Omega$  a gain of 1 at 50 $\Omega$  is

achieved together with RD1 and RD2.

RD1, RD2  $450\Omega$  CS1, CS2 100 nF CS3, CS4 100 nF

## 7. Description of the Evaluation Board

Board material: epoxy;  $\varepsilon r = 4.8$ , thickness = 0.5 mm, transmission lines:  $Z_{\Omega} = 50\Omega$ 

The board offers the following functions:

- Test circuit for the U2794B:
  - The supply voltage and the control inputs GC, PC and PU are connected via a plug strip. The control input voltages can be generated via external potentiometers; then the inputs should be AC-grounded (time requirements in burst mode for power up have to be considered).
  - The outputs I, IX, Q, QX are DC coupled via an plug strip or can be AC-connected via SMB plugs for high frequency tests e.g. noise figure or s-parameter measurement. The Pins II, IIX, QQ, QQX allow user-definable filtering with 2 external capacitors CII, CQQ.
  - The offsets of both channels can be adjusted with two potentiometers or resistors.
  - The LO- and the RF-inputs are AC-coupled and connected via SMB plugs. If transmission line T3 is connected to the RF-input and AC-grounded at the other end, gain and noise performance can be improved (input matching to 50Ω).
  - The complementary RF-input is AC-coupled to GND (CRFX = 1 nF), the same appears to the complementary LO input (CNLO = 1 nF).
- A calibration part which allows to calibrate an s-parameter analyzer directly to the in- and output- signal ports of the U2794B.
- For single-ended measurements at the demodulator outputs, two OPs (e.g., AD620 or other) can be configured with programmable gain; together with an output-divider network RD =  $450\Omega$  to RL =  $50\Omega$ , direct measurements with  $50\Omega$  load impedances are possible at frequencies t < 100 kHz.

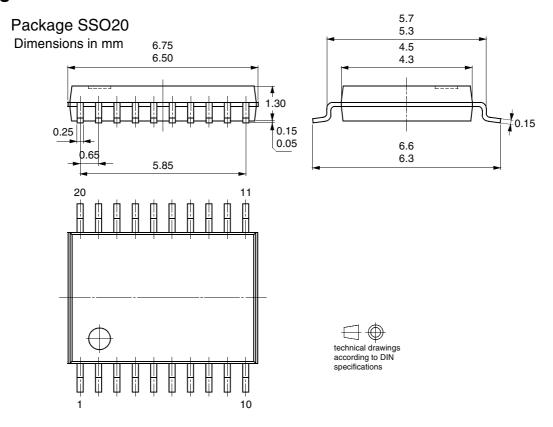




# 8. Ordering Information

Extended Type Number	Package	Remarks		
U2794B-NFSH	SSO20	Tube, MOQ 830 pcs, Pb-free		
U2794B-NFSG3H	SSO20	Taped and reeled, MOQ 4000 pcs, Pb-free		

# 9. Package Information





## **Atmel Corporation**

2325 Orchard Parkway San Jose, CA 95131, USA Tel: 1(408) 441-0311 Fax: 1(408) 487-2600

### **Regional Headquarters**

### Europe

Atmel Sarl Route des Arsenaux 41 Case Postale 80 CH-1705 Fribourg Switzerland

Tel: (41) 26-426-5555 Fax: (41) 26-426-5500

#### Asia

Room 1219 Chinachem Golden Plaza 77 Mody Road Tsimshatsui East Kowloon Hong Kong

Tel: (852) 2721-9778 Fax: (852) 2722-1369

#### Japan

9F, Tonetsu Shinkawa Bldg. 1-24-8 Shinkawa Chuo-ku, Tokyo 104-0033 Japan

Tel: (81) 3-3523-3551 Fax: (81) 3-3523-7581

### **Atmel Operations**

#### Memory

2325 Orchard Parkway San Jose, CA 95131, USA Tel: 1(408) 441-0311 Fax: 1(408) 436-4314

#### Microcontrollers

2325 Orchard Parkway San Jose, CA 95131, USA Tel: 1(408) 441-0311 Fax: 1(408) 436-4314

La Chantrerie BP 70602 44306 Nantes Cedex 3, France Tel: (33) 2-40-18-18-18 Fax: (33) 2-40-18-19-60

### ASIC/ASSP/Smart Cards

Zone Industrielle 13106 Rousset Cedex, France Tel: (33) 4-42-53-60-00 Fax: (33) 4-42-53-60-01

1150 East Cheyenne Mtn. Blvd. Colorado Springs, CO 80906, USA

Tel: 1(719) 576-3300 Fax: 1(719) 540-1759

Scottish Enterprise Technology Park Maxwell Building East Kilbride G75 0QR, Scotland

Tel: (44) 1355-803-000 Fax: (44) 1355-242-743

#### RF/Automotive

Theresienstrasse 2 Postfach 3535 74025 Heilbronn, Germany Tel: (49) 71-31-67-0 Fax: (49) 71-31-67-2340

1150 East Cheyenne Mtn. Blvd. Colorado Springs, CO 80906, USA

Tel: 1(719) 576-3300 Fax: 1(719) 540-1759

Biometrics/Imaging/Hi-Rel MPU/ High Speed Converters/RF Datacom

Avenue de Rochepleine BP 123

38521 Saint-Egreve Cedex, France

Tel: (33) 4-76-58-30-00 Fax: (33) 4-76-58-34-80

Literature Requests www.atmel.com/literature

Disclaimer: The information in this document is provided in connection with Atmel products. No license, express or implied, by estoppel or otherwise, to any intellectual property right is granted by this document or in connection with the sale of Atmel products. EXCEPT AS SET FORTH IN ATMEL'S TERMS AND CONDITIONS OF SALE LOCATED ON ATMEL'S WEB SITE, ATMEL ASSUMES NO LIABILITY WHATSOEVER AND DISCLAIMS ANY EXPRESS, IMPLIED OR STATUTORY WARRANTY RELATING TO ITS PRODUCTS INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTY OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE, OR NON-INFRINGEMENT. IN NO EVENT SHALL ATMEL BE LIABLE FOR ANY DIRECT, INDIRECT, CONSEQUENTIAL, PUNITIVE, SPECIAL OR INCIDENTAL DAMAGES (INCLUDING, WITHOUT LIMITATION, DAMAGES FOR LOSS OF PROFITS, BUSINESS INTERRUPTION, OR LOSS OF INFORMATION) ARISING OUT OF THE USE OR INABILITY TO USE THIS DOCUMENT, EVEN IF ATMEL HAS BEEN ADVISED OF THE POSSIBILITY OF SUCH DAMAGES. Atmel makes no representations or warranties with respect to the accuracy or completeness of the contents of this document and reserves the right to make changes to specifications and product descriptions at any time without notice. Atmel does not make any commitment to update the information contained herein. Unless specifically provided otherwise, Atmel products are not suitable for, and shall not be used in, automotive applications. Atmel's products are not intended, authorized, or warranted for use as components in applications intended to support or sustain life.

© Atmel Corporation 2005. All rights reserved. Atmel<sup>®</sup>, logo and combinations thereof, Everywhere You Are<sup>®</sup> and others, are registered trademarks or trademarks of Atmel Corporation or its subsidiaries. Other terms and product names may be trademarks of others.

